

20V Dual N-Channel MOSFET



TSSOP-8

Pin Definition:

8 1. D 2. S 3. S 4. G

1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2

4. Gate 1 5. Gate 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
20	30 @ V _{GS} = 4.5V	6.0	
	40 @ V _{GS} = 2.5V	5.2	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

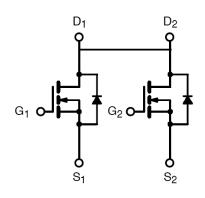
Application

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM6866DCA RV	TSSOP-8	T&R

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current		I _D	6	А	
Pulsed Drain Current			30	А	
Continuous Source Current (Diode Co	nduction) ^{a,b}	I _S	1.7	А	
Maximum Dougr Dissipation	Ta = 25 °C	D	1.6	W	
Maximum Power Dissipation	Ta = 75 °C	P _D	1.1	VV	
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit		
Junction to Case Thermal Resistance	R⊖ _{JC}	40	°C/W		
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ _{JA}	77	°C/W		

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.



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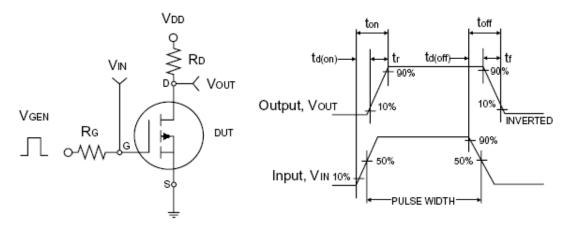


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6			V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 6.0A$	В		21	30	mΩ
Diain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.2A$	R _{DS(ON)}		30	40	
Forward Transconductance	$V_{DS} = 10V, I_D = 6A$	g _{fs}		30		S
Diode Forward Voltage	$I_{S} = 1.7A, V_{GS} = 0V$	V_{SD}		0.7	1.2	V
Dynamic ^b		_				
Total Gate Charge	\/ - 10\/ - 6A	Q_g		4.86		
Gate-Source Charge	$I_S = 1.7A, V_{GS} = 0V$ $V_{DS} = 10V, I_D = 6A, V_{GS} = 4.5V$	Q_gs		0.92		nC
Gate-Drain Charge	$V_{GS} = 4.5V$ Q_{gd}			1.4		
Input Capacitance	\/ - 0\/ \/ - 0\/	C _{iss}		562		
Output Capacitance	$V_{DS} = 8V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		106		pF
Reverse Transfer Capacitance	1 - 1.0101112	C _{rss}		75		
Switching ^c						
Turn-On Delay Time	V -40V D -400	t _{d(on)}		8.1		
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$	t _r		9.95		nS
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 4.5V,$ $R_G = 6\Omega$	$t_{d(off)}$		21.85		113
Turn-Off Fall Time	1/G - 077	t _f		5.35		

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

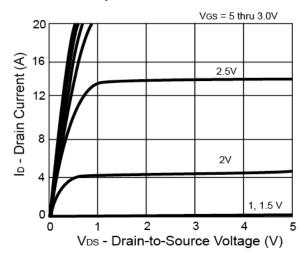


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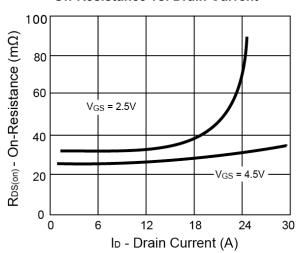


Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

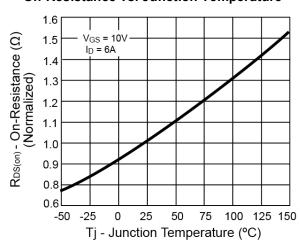
Output Characteristics



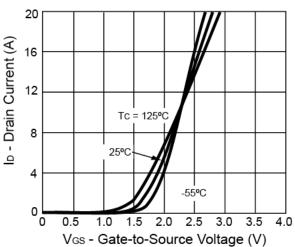
On-Resistance vs. Drain Current



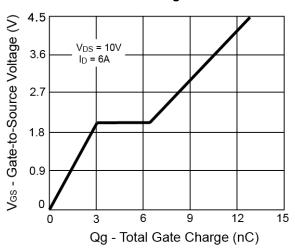
On-Resistance vs. Junction Temperature



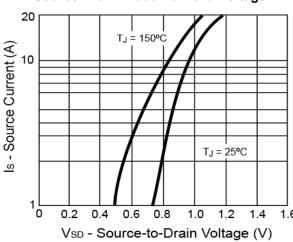
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



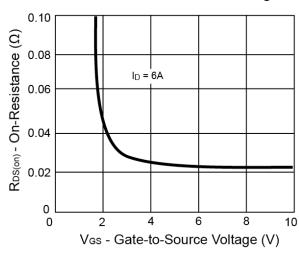


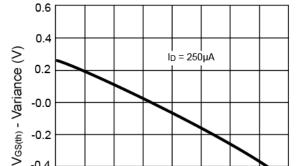
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Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage





0

25

50

Tj - Junction Temperature (°C)

75

100

125 150

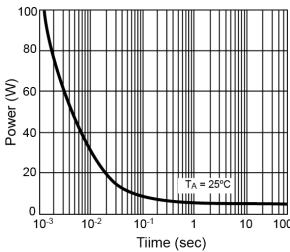
-0.2

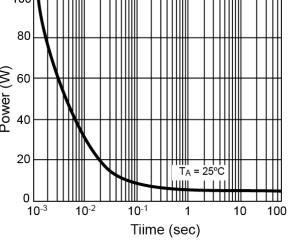
-0.4

-0.6 -50 -25

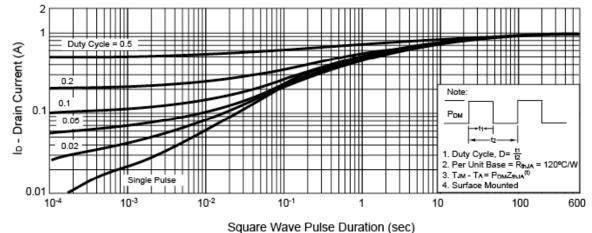
Threshold Voltage

Single Pulse Power





Normalized Thermal Transient Impedance, Junction-to-Ambient

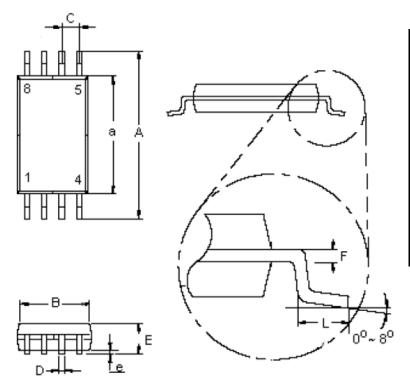




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TSSOP-8 Mechanical Drawing



TSSOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	6.20	6.60	0.244	0.260	
а	4.30	4.50	0.170	0.177	
В	2.90	3.10	0.114	0.122	
C	0.65 (typ)		0.025 (typ)		
D	0.25	0.30	0.010	0.019	
Е	1.05	1.20	0.041	0.049	
е	0.05	0.15	0.002	0.009	
F	0.127		0.005		
L	0.50	0.70	0.020	0.028	



TSM6866D 20V Dual N-Channel MOSFET

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